

CN870-80
INFRARED LED CHIP
 <Specifications>

Commodity Type and Physical Characteristics	
Material	GaAlAs/GaAlAs(DDH)
Top Side P(anode)side	Au Alloy
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	120um dia.
Chip Size	800um x 800um
Chip Thickness	150um ± 30um

Electro-Optical Characteristics[Ta=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA		1.40	1.45	V
		IF=100mA		1.48	1.50	
		IF=1A*		2.2	2.8	
		IF=2A*		3.6	4.2	
		IF=4A*		4.2	4.8	
Reverse Current	IR	VR=5V			10	uA
Radiated Power	PO	IF=50mA		8.5		mW
		IF=100mA		17		
		IF=1A*		170		
		IF=2A*		340		
		IF=4A*		680		
Peak Wavelength	λP	IF=50mA		870		nm
Spectral Radiation Bandwidth	$\Delta\lambda$	IF=50mA		40		nm
Rise Time	tr	IF=50mA		15		ns
Fall Time	tf	IF=50mA		10		ns

Die shall be mounted on TO-18 gold header without resin coated.

* Pulse Forward Current condition: Duty=1% and Pulse Width=10µs.

